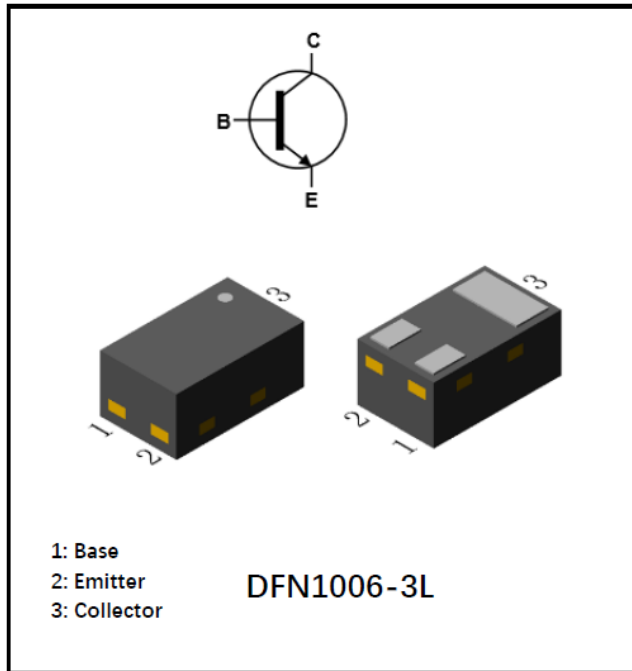


## NPN General Purpose Transistor



### Features

- Lead Free Finish/RoHS Compliant
- Small package saves board space
- Moisture Sensitivity Level 3

### Mechanical Data

- **Package:** DFN1006-3L
- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD22-B102
- **Marking:** D5

### ■Maximum Ratings (Ta=25°C Unless otherwise specified)

Symbol	Parameter	Value	Unit
VCBO	Collector-Base Voltage	50	V
VCEO	Collector-Emitter Voltage	45	V
VEBO	Emitter-Base Voltage	6	V
IC	Collector Current	100	mA
PC	Collector Power Dissipation	100	mW
Tj	Junction Temperature	-55~+150	°C
Tstg	Storage Temperature	-55~+150	°C

### ■Ordering Information (Example)

PREFERRED P/N	UNIT WEIGHT(mg)	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
BC847BM	Approximate 0.89	10K	100K	400K	Tape & Reel



# BC847BM

## ■Electrical Characteristics (T<sub>a</sub>=25°C Unless otherwise specified)

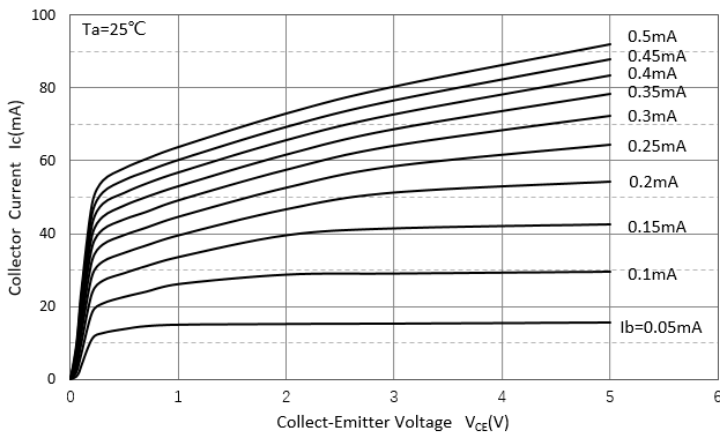
Parameter	Symbol	Test conditions	Min	TYP	Max	Unit
Collector-base breakdown voltage	V <sub>CBO</sub>	IC= 10μA, IE=0	50	-	-	V
Collector-emitter breakdown voltage	V <sub>CEO</sub>	IC= 10mA, IB=0	45	-	-	V
Emitter-base breakdown voltage	V <sub>EBO</sub>	IE= 10μA, IC=0	6	-	-	V
Collector-base cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =30 V ,IE=0	-	-	15	nA
Emitter-base cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =5 V , IC=0	-	-	100	nA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 5V, IC= 2mA	200	-	450	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	IC=10mA, IB= 0.5mA	-	-	200	mV
	V <sub>CE(sat)</sub>	IC=100mA, IB= 5mA	-	-	400	mV
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	IC=100mA, IB= 5mA	-	0.9	1.1	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> = 5V, IC= 2mA	580	-	700	mV
	V <sub>BE</sub>	V <sub>CE</sub> =5V, IC= 10mA	-	-	770	mV
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =5V, IC= 10mA f=100MHz	100	-	-	MHz
Collector-base output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V,f=1MHz	-	-	4.5	pF



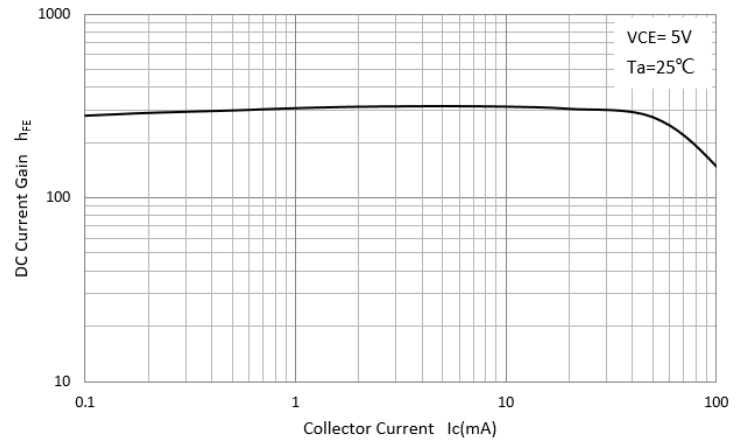
# BC847BM

## ■ Characteristics (Typical)

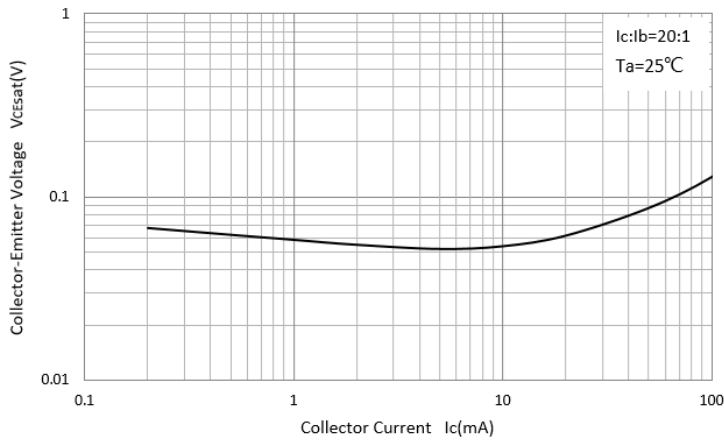
Static Characteristic



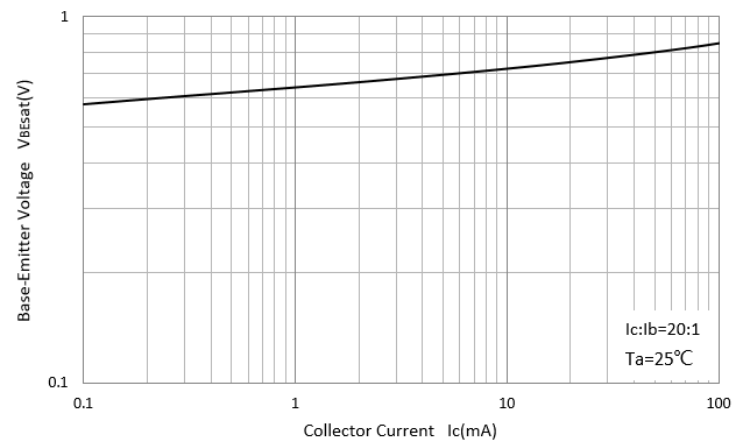
DC Current Gain



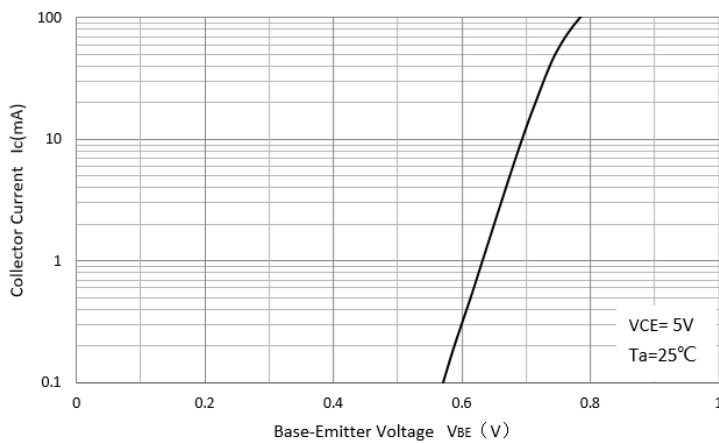
Collector-Emitter Saturation Voltage



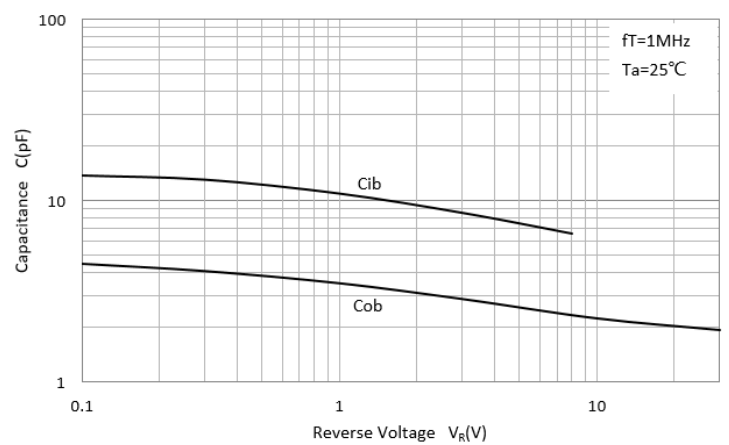
Base-Emitter Saturation Voltage



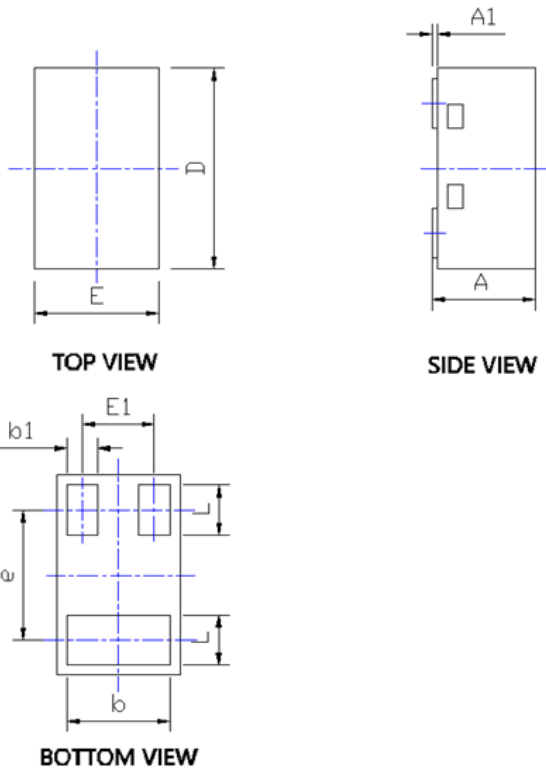
Base-Emitter On Voltage



$C_{ob}/C_{ib}-V_{CB}/V_{EB}$

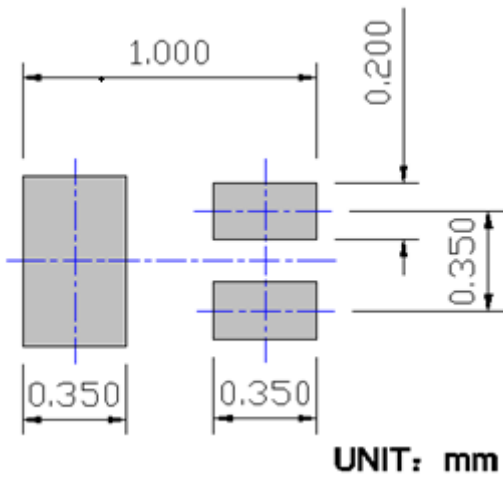


## ■ Outline Dimensions



DIMENSIONS			
SYMBOL	Millimeter		
	MIN.	NOM.	MAX.
A	0.42	---	0.55
A1	0.025REF		
b	0.45	0.50	0.55
b1	0.10	0.15	0.20
D	0.95	1.00	1.05
E	0.55	0.60	0.65
E1	0.35BSC		
e	0.65BSC		
L	0.20	0.25	0.30

## ■ Soldering Footprint





## BC847BM

---

### Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website [http:// www.21yangjie.com](http://www.21yangjie.com) , or consult your nearest Yangjie's sales office for further assistance.